

Amendments to the Specification

Please replace paragraph [0001] at page 1 of the specification with the following new paragraph [0001]:

[0001] This application is a continuation-in-part of U.S. Patent Application No. 10/379,466, filed 4 March 2003, now U.S. Patent No. 7,098,149, the disclosure of which is incorporated herein by reference in its entirety.

Please replace paragraph [0044] at page 12 of the specification with the following new paragraph [0044]:

[0044] In a certain preferred embodiment of the present invention wherein the organosilicate glass film consists essentially of Si, C, O, H, and optionally F, the film is formed by providing a substrate within a vacuum chamber; introducing into the vacuum chamber chemical reagents that comprise at least one structure-former precursor selected from the group consisting of an organosilane and an organosiloxane, and optionally a pore-former precursor distinct from the at least one structure-former precursor; and applying energy to the reagents in said chamber to induce reaction of the reagents and to form the film on the substrate. Examples of chemical reagents used as structure-former and pore-former precursors may be found in pending U. S. Patent Applications Attorney Docket Nos. ~~06063USA, 06274PUSA, 06150USA, and 06336PUSA~~ Nos. 6,583,048, 6,846,515, and 6,716,770, and U.S. patent application Publication No. 2004/0096593 A1, which are commonly assigned to the assignee of the present invention and incorporated herein by reference in ~~its~~ their entirety.

Please replace paragraph [0055] at page 16 to page 17 of the specification with the following new paragraph [0055]:

[0055] In certain embodiments of the present invention, a single compound may function as both the structure-former and pore-former within the porous OSG film. That is, the structure-former precursor and the pore-former precursor are not necessarily different compounds, and in certain embodiments, the pore-former is a part of (e.g., covalently bound to) the structure-former precursor. Examples of these materials may be found, for example, in pending U. S. Patent Applications, Attorney Docket Nos. ~~06150~~USA 6,716,770 and ~~06274~~USA 6,846,515, that are commonly assigned to the assignee of the present invention and incorporated herein by reference in ~~its~~ their entirety. For example, it is possible to use 1-neohexyl-1,3,5,7-tetramethyl-cyclotetrasiloxane ("neohexyl TMCTS") as a single species, whereby the TMCTS portion of the molecule forms the base OSG structure and the bulky alkyl substituent neohexyl is the pore-former species which is removed, for example, during the anneal process. Having the pore-former attached to a Si species that will network into the OSG structure may be advantageous in achieving a higher efficiency of incorporation of pore-former into the film during the deposition process. Furthermore, it may also be advantageous to have two pore-formers attached to one Si in the precursor, such as in di-neohexyl-diethoxysilane, or two Si's attached to one pore-former, such as in 1,4-bis(diethoxysilyl)cyclohexane. While not intending to be bound by theory, the reaction of one Si-pore-former bond in the plasma may enable the the incorporation of the second pore-former group into the deposited film.

Please replace paragraph [0079] at page 23 to page 24 of the specification with the following new paragraph [0079]:

[0079] The present invention also discloses a mixture for forming a dense or a porous OSG film having a dielectric constant of 3.5 or below suitable for exposure to UV light. The OSG film may be formed by a variety of deposition processes including CVD-related and spin-on-glass processes. For dense OSG films, the mixture comprises at least one structure-former precursor and/or resultant OSG film that exhibits an absorbance in the 200 to 400 nm wavelength range. For porous OSG films, the mixture may comprise from 5% to 95% by weight of a structure-former precursor and from 5% to 95% by weight of a pore-former precursor wherein the at least one of the precursors and/or the organosilicate film exhibits an absorbance in the 200 to 400 nm wavelength range. Depending upon the deposition process, such as for spin-on-glass deposition, the mixture may comprise additional additives, for example, a solvent, a catalyst, a surfactant, water, and the like. Additional additives to the mixture used for spin-on-glass deposition may be found, for example, in pending U. S. ~~Patent Applications Attorney Docket No. 06336PUSA~~ patent application Publication No. 2004/0096593 A1, which is commonly assigned to the assignee of the present invention and incorporated herein by reference in its entirety.